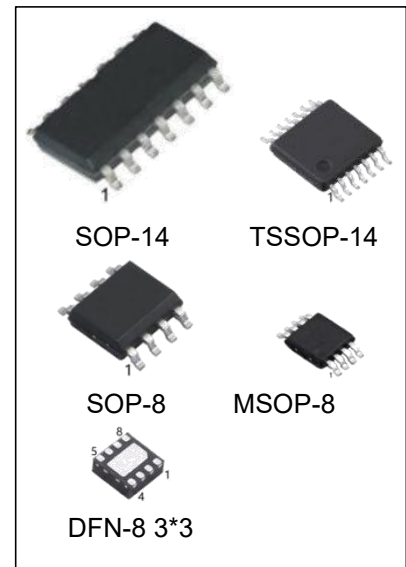


48V, Low Noise, Precision Operational Amplifiers

Features and Benefits

- Wide Supply: ± 2.25 V to ± 24 V, 4.5 V to 48 V
- Low Offset Voltage: ± 100 μ V Maximum
- Low Offset Voltage Drift: ± 1 μ V/ $^{\circ}$ C
- Bandwidth: 1.1 MHz GBW
- Slew Rate: 0.8 V/ μ s
- Low Noise: 22 nV/ $\sqrt{\text{Hz}}$ at 10 kHz
- High Common-Mode Rejection: 110 dB
- Low Bias Current: ± 20 pA
- EMI/RFI Filtered Inputs



Ordering Information

DEVICE	Package Type	MARKING	Packing	Packing Qty
ISL28108FM/TR-HG	SOP-8	28108	REEL	2500pcs/reel
ISL28108FMM/TR-HG	MSOP-8	28108	REEL	3000pcs/reel
ISL28108FDQ3/TR-HG	DFN-8 3*3	28108	REEL	5000pcs/reel
ISL28208M/TR-HG	SOP-8	28208	REEL	2500pcs/reel
ISL28208MM/TR-HG	MSOP-8	28208	REEL	3000pcs/reel
ISL28208DQ3/TR-HG	DFN-8 3*3	28208	REEL	5000pcs/reel
ISL28408M/TR-HG	SOP-14	28408	REEL	2500pcs/reel
ISL28408MT/TR-HG	TSSOP-14	28408	REEL	2500pcs/reel

General Description

The ISL28x08 is a new generation of high voltage (48 V), low noise, precision operational amplifiers. These devices offer outstanding dc precision and ac performance, include low offset ($\pm 100 \mu\text{V}$ maximum), low drift ($\pm 1 \mu\text{V}/^\circ\text{C}$), 1.1-MHz bandwidth, and 22 nV/ $\sqrt{\text{Hz}}$ Input voltage noise density at 10 kHz. Unique features such as differential input-voltage range to the negative supply rail, high output current ($\pm 40 \text{ mA}$), and high capacitive load drive of up to 1 nF make the ISL28x08 high-performance op-amps for high-voltage industrial applications.

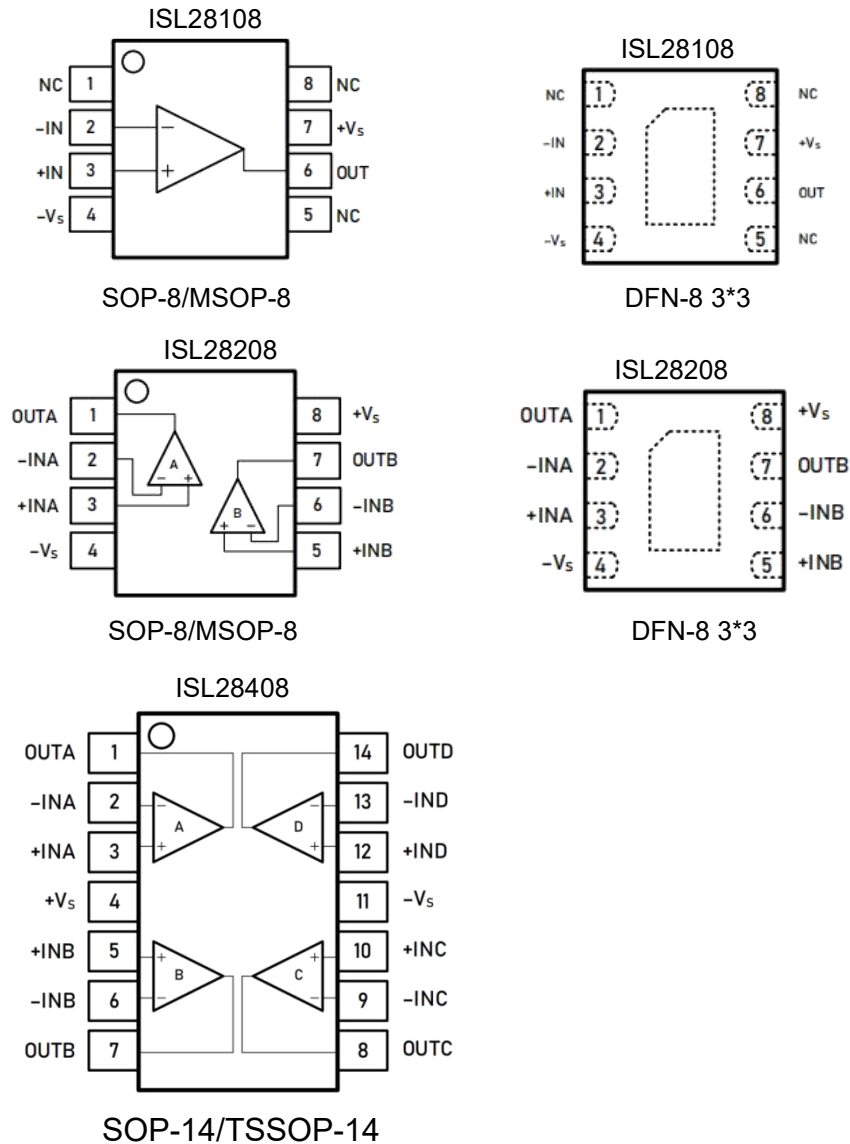
The robust design of the ISL28x08 family provides ease-of-use to the circuit designer: integrated RF/EMI rejection filter, no phase reversal in overdrive conditions, and high electro-static discharge (ESD) protection. The ISL28x08 are optimized for operation at voltages from +4.5 V ($\pm 2.25 \text{ V}$) to +48 V ($\pm 24 \text{ V}$) over the extended temperature range of -40°C to $+125^\circ\text{C}$.

The ISL28108 (single) is available in both SOP-8, MSOP-8 and DFN-8 packages. The ISL28208 (dual) is offered in SOP-8, MSOP-8 and DFN-8 packages. The quad-channel ISL28408 is offered in both SOP-14 and TSSOP-14 packages.

Applications

- High-side and low-side current sensing
- Analog input and output modules
- ADC driver and reference buffer amplifier
- High Precision Comparator
- Power delivery: UPS, server, and merchant network power
- Multiplexed Data-Acquisition Systems
- Test and Measurement Equipment
- Programmable Logic Controllers

Pin Configuration (Top View)



Pin Description

Symbol	Description
-IN	Inverting input of the amplifier. The voltage range is from V_{S-} to $V_{S+} - 2V$.
+IN	Non-inverting input of the amplifier. This pin has the same voltage range as -IN.
+V _S	Positive power supply. The voltage is from 4.5V to 48V. Split supplies are possible as long as the voltage between V_{S+} and V_{S-} is from 4.5V to 48V.
-V _S	Negative power supply. It is normally tied to ground. It can also be tied to a voltage other than ground as long as the voltage between V_{S+} and V_{S-} is from 4.5V to 48V.
OUT	Amplifier output.
NC	No connection

Limiting Value

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Absolute Maximum Rating
Supply Voltage, VS+ to VS-	60 V
Signal Input Terminals: Voltage, Current	-VS - 0.3V to +VS + 0.3V, ±10 mA
Output Short-Circuit	Continuous
Storage Temperature Range, Tstg	-65 °C to +150 °C
Operating Temperature Range, TA	-40 °C to +125 °C
Junction Temperature, TJ	150 °C
Lead Temperature Range (Soldering 10 sec)	260 °C

Note: Stress greater than those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification are not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

ESD Rating

Parameter	Item	Value	Unit
Electrostatic Discharge Voltage	Human body model (HBM), per MIL-STD-883J / Method 3015.9 ⁽¹⁾	±1 500	V
	Charged device model (CDM), per ESDA/JEDEC JS-002-2014 ⁽²⁾	±1 000	
	Machine model (MM), per JESD22-A115C	±400	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible if necessary precautions are taken.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible if necessary precautions are taken.

Electrical Characteristics

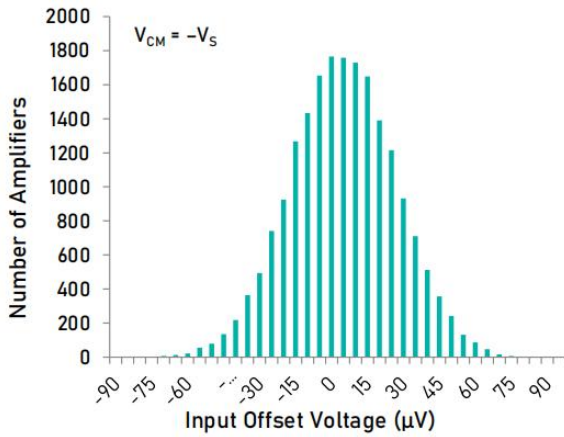
$V_S = 4.5\text{ V to }48\text{ V}$, $T_A = +25\text{ }^\circ\text{C}$, $V_{CM} = V_S/2$, $V_O = V_S/2$, and $R_L = 10\text{ k}\Omega$ connected to $V_S/2$, unless otherwise noted. Boldface limits apply over the specified temperature range, $T_A = -40\text{ }^\circ\text{C to }+125\text{ }^\circ\text{C}$.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
OFFSET VOLTAGE						
V_{OS}	Input offset voltage				± 100	μV
V_{OSTC}	Offset voltage drift	$T_A = -40\text{ to }+125\text{ }^\circ\text{C}$		± 1		$\mu\text{V}/^\circ\text{C}$
PSRR	Power supply rejection ratio	$V_S = 4.5\text{ to }44\text{ V}$, $V_{CM} = 0.1\text{ V}$		2		$\mu\text{V}/\text{V}$
		$T_A = -40\text{ to }+125\text{ }^\circ\text{C}$		6		
INPUT BIAS CURRENT						
I_B	Input bias current			20		pA
		$T_A = +85\text{ }^\circ\text{C}$		150		
		$T_A = +125\text{ }^\circ\text{C}$		600		
I_{OS}	Input offset current			10		pA
NOISE						
V_n	Input voltage noise	$f = 0.1\text{ to }10\text{ Hz}$		4		μV_{P-P}
e_n	Input voltage noise density	$f = 1\text{ kHz}$		25		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 10\text{ kHz}$		22		
I_n	Input current noise density	$f = 1\text{ kHz}$		5		$\text{fA}/\sqrt{\text{Hz}}$
INPUT VOLTAGE						
V_{CM}	Common-mode voltage range		$-V_S$		$+V_S - 2$	V
CMRR	Common-mode rejection ratio	$V_S = 40\text{ V}$, $V_{CM} = 0\text{ to }38\text{ V}$		110		dB
		$V_{CM} = 0.1\text{ to }38\text{ V}$, $T_A = -40\text{ to }+125\text{ }^\circ\text{C}$		98		
		$V_S = 5.0\text{ V}$, $V_{CM} = 0\text{ to }3\text{ V}$		85		
		$V_{CM} = 0.1\text{ to }3\text{ V}$, $T_A = -40\text{ to }+125\text{ }^\circ\text{C}$		72		
INPUT IMPEDANCE						
CIN	Input capacitance	Differential		2.0		pF
		Common mode		3.5		
OPEN-LOOP GAIN						
A_{VOL}	Open-loop voltage gain	$V_S = 40\text{ V}$, $V_O = 0.1\text{ to }39.9\text{ V}$		116		dB
		$T_A = -40\text{ to }+125\text{ }^\circ\text{C}$		112		
		$V_S = 5\text{ V}$, $V_O = 0.1\text{ to }4.9\text{ V}$		101		
		$T_A = -40\text{ to }+125\text{ }^\circ\text{C}$		97		
FREQUENCY RESPONSE						
GBW	Gain bandwidth product			1.1		MHz
SR	Slew rate	$V_S = 40\text{ V}$, $G = +1$, 10 V step		0.8		$\text{V}/\mu\text{s}$

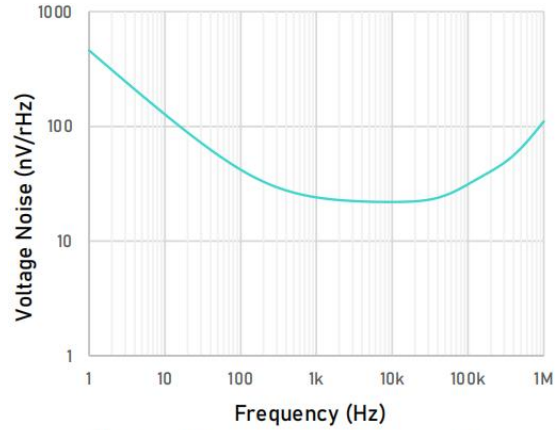
THD+N	Total harmonic distortion + noise	$G = +1, f = 1 \text{ kHz}, V_O = 3 \text{ VRMS}$		0.02		%
t_s	Settling time	To 0.1%, $V_S = 40 \text{ V}, G = +1, 5 \text{ V step}$		6		μs
		To 0.01%, $V_S = 40 \text{ V}, G = +1, 5 \text{ V step}$		12		
t_{OR}	Overload recovery time	$V_{IN} \times \text{Gain} > V_S$		3		μs
OUTPUT						
V_{OH}	High output voltage swing	$V_S = \pm 20 \text{ V}, R_L = 10 \text{ k}\Omega$		$+V_S - 97$		mV
		$V_S = \pm 20 \text{ V}, R_L = 2 \text{ k}\Omega$		$+V_S - 257$		
V_{OL}	Low output voltage swing	$V_S = \pm 20 \text{ V}, R_L = 10 \text{ k}\Omega$		$-V_S + 52$		mV
		$V_S = \pm 20 \text{ V}, R_L = 2 \text{ k}\Omega$		$-V_S + 232$		
I_{SC}	Short-circuit current			± 40		mA
POWER SUPPLY						
V_S	Operating supply voltage	$T_A = -40 \text{ to } +125 \text{ }^\circ\text{C}$	4.5		48	V
I_Q	Quiescent current (per amplifier)	$V_S = 5 \text{ V}$		150		μA
		$V_S = 40 \text{ V}$		220		
THERMAL CHARACTERISTICS						
θ_{JA}	Package Thermal Resistance	MSOP-8		201		$^\circ\text{C/W}$
		SOP-8		125		
		DFN-8		65		
		SOP-14		115		
		TSSOP-14		112		

Typical Performance Characteristics

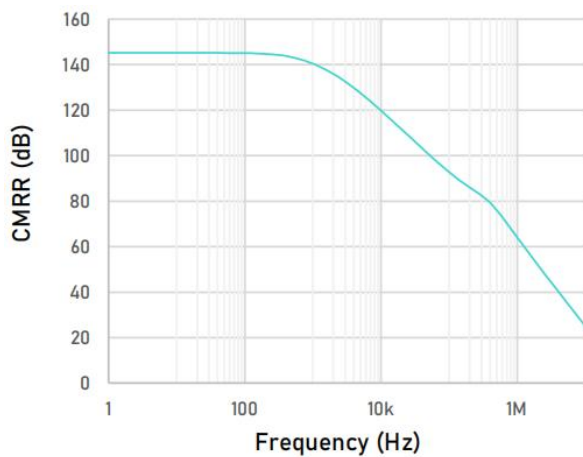
At $T_A = +25\text{ }^\circ\text{C}$, $V_{CM} = V_S / 2$, and $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, unless otherwise noted.



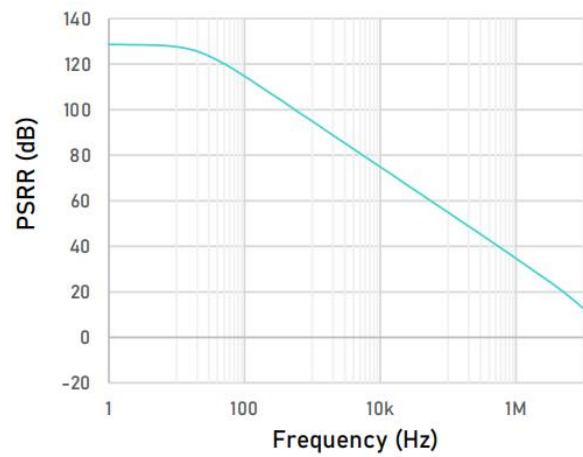
Offset Voltage Production Distribution



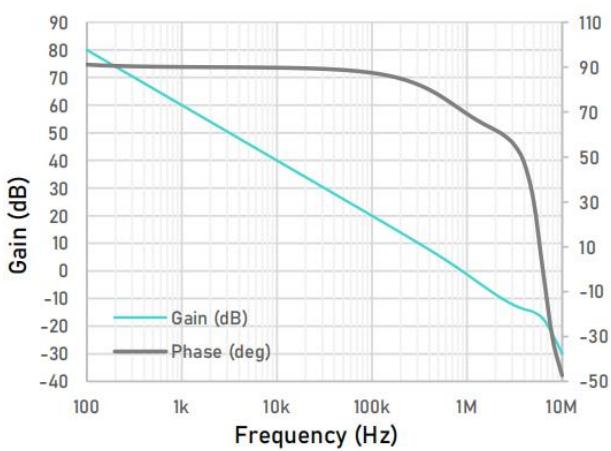
Input Voltage Noise Spectral Density as a function of Frequency



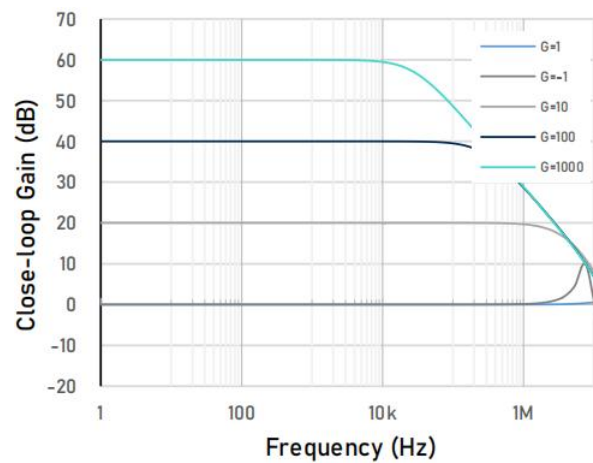
CMRR as a function of Frequency



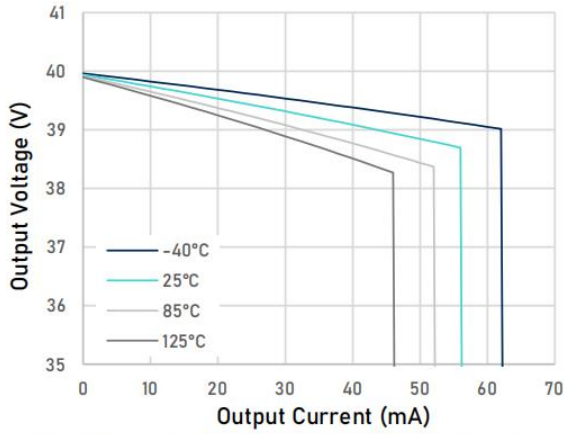
PSRR as a function of Frequency



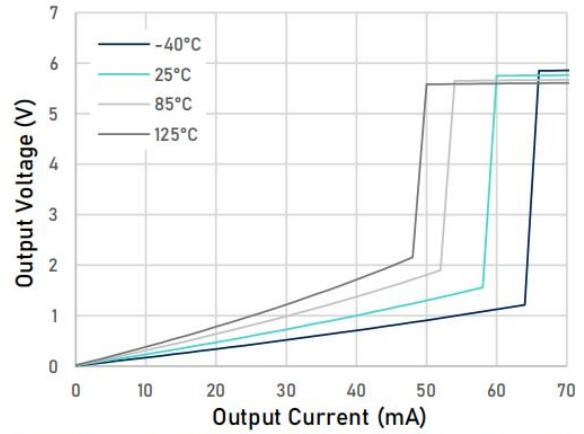
Open-loop Gain and Phase as a function of Frequency



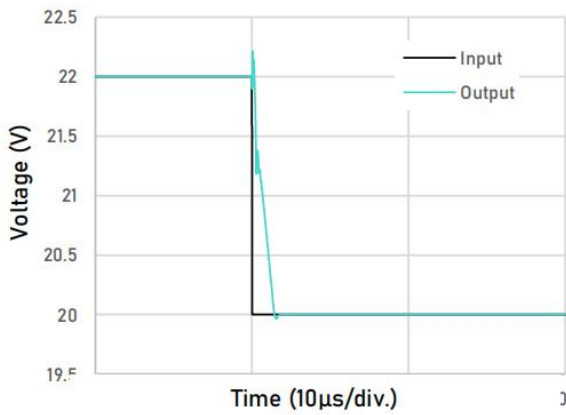
Close-loop Gain as a function of Frequency



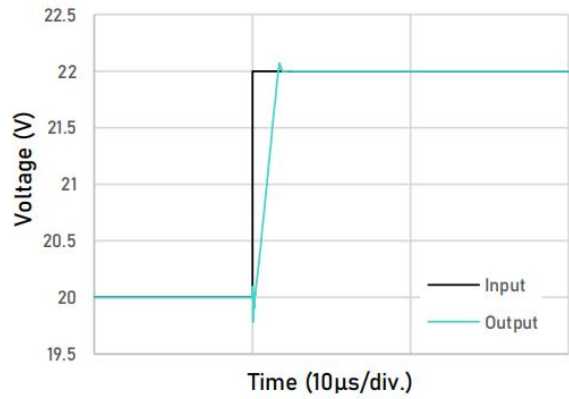
Output Voltage Swing as a function of Output Current (Sourcing, $V_S = 40\text{ V}$)



Output Voltage Swing as a function of Output Current (Sinking, $V_S = 40\text{ V}$)



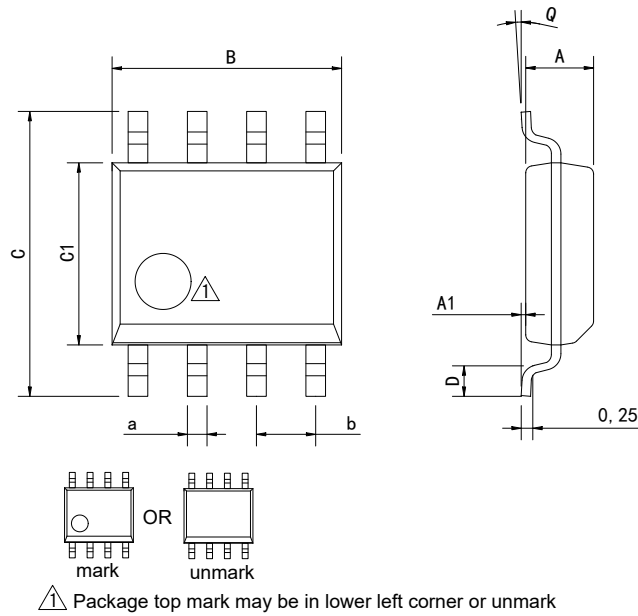
Large-Signal Step Response(Failing)



Large-Signal Step Response(Rising)

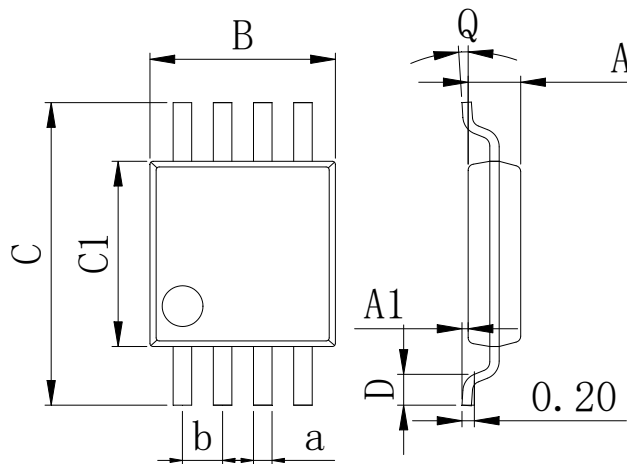
Physical Dimensions

SOP-8



Dimensions In Millimeters(SOP-8)									
Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	1.35	0.05	4.90	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	5.10	6.20	4.00	0.80	8°	0.45	

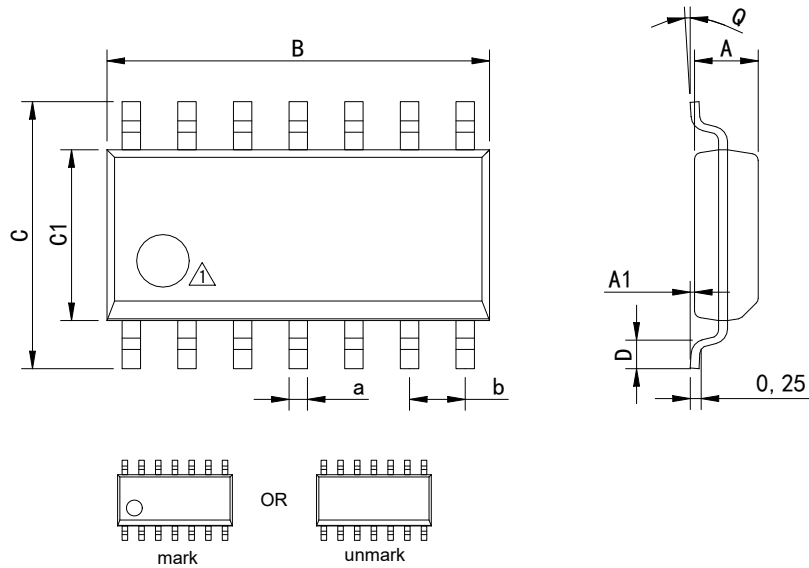
MSOP-8



Dimensions In Millimeters(MSOP-8)									
Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	0.80	0.05	2.90	4.75	2.90	0.35	0°	0.25	0.65 BSC
Max:	0.90	0.20	3.10	5.05	3.10	0.75	8°	0.35	

Physical Dimensions

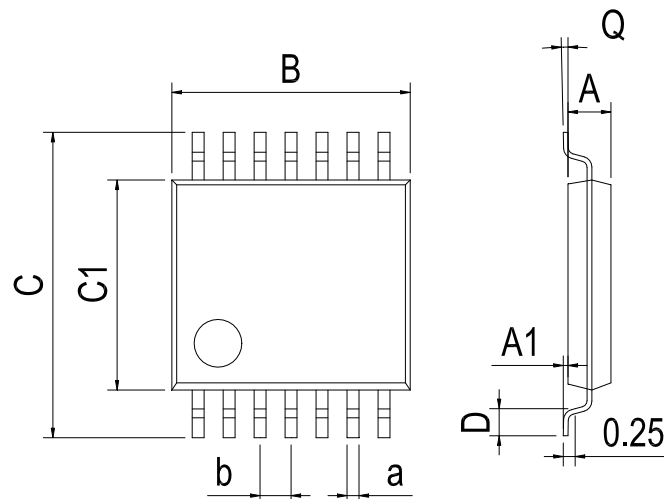
SOP-14



△ Package top mark may be in lower left corner or unmark

Dimensions In Millimeters(SOP-14)									
Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	1.35	0.05	8.55	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	8.95	6.20	4.00	0.80	8°	0.45	

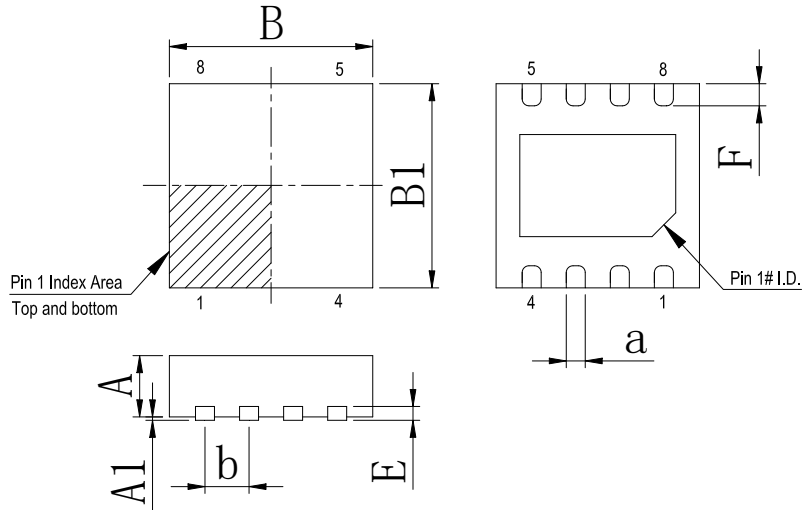
TSSOP-14



Dimensions In Millimeters(TSSOP-14)									
Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	0.85	0.05	4.90	6.20	4.30	0.40	0°	0.20	0.65 BSC
Max:	0.95	0.20	5.10	6.60	4.50	0.80	8°	0.25	

Physical Dimensions

DFN-8 3*3



Dimensions In Millimeters(DFN-8 3*3)								
Symbol:	A	A1	B	B1	E	F	a	b
Min:	0.85	0.00	2.90	2.90	0.20	0.30	0.20	0.65 BSC
Max:	0.95	0.05	3.10	3.10	0.25	0.50	0.34	

Revision History

REVISION NUMBER	DATE	REVISION	PAGE
V1.0	2018-11	New	1-10
V1.1	2025-6	Document Reformatting	1-12
V1.2	2025-12	Update important statements	12

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